

FCPF260N60E_F152

N-Channel SuperFET® II MOSFET

600 V, 15 A, 260 mΩ

Features

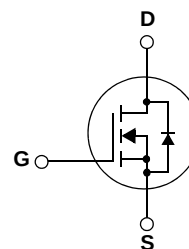
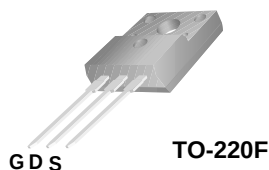
- 650 V @ $T_J = 150^\circ\text{C}$
- Max. $R_{DS(on)} = 260\text{ m}\Omega$
- Ultra Low Gate Charge (Typ. $Q_g = 48\text{ nC}$)
- Low Effective Output Capacitance (Typ. $C_{oss,eff} = 129\text{ pF}$)
- 100% Avalanche Tested

Applications

- LCD / LED / PDP TV Lighting
- Solar Inverter
- AC-DC Power Supply

Description

SuperFET® II MOSFET is Fairchild Semiconductor®'s first generation of high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This advanced technology is tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate and higher avalanche energy. Consequently, SuperFET® II MOSFET is suitable for various AC/DC power conversion for system miniaturization and higher efficiency.



MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	FCPF260N60E_F152	Unit
V_{DSS}	Drain to Source Voltage	600	V
V_{GSS}	Gate to Source Voltage	- DC	± 20 V
		- AC (f > 1Hz)	± 30 V
I_D	Drain Current	- Continuous ($T_C = 25^\circ\text{C}$)	15* A
		- Continuous ($T_C = 100^\circ\text{C}$)	9.5* A
I_{DM}	Drain Current	- Pulsed (Note 1)	45* A
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	292.5 mJ
I_{AR}	Avalanche Current	(Note 1)	3.0 A
E_{AR}	Repetitive Avalanche Energy	(Note 1)	1.56 mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	20 V/ns
	MOSFET dv/dt		100 V/ns
P_D	Power Dissipation	($T_C = 25^\circ\text{C}$)	36 W
		- Derate above 25°C	0.29 W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

*Drain current limited by maximum junction temperature

Thermal Characteristics

Symbol	Parameter	FCPF260N60E_F152	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case	3.5	$^\circ\text{C/W}$
$R_{\theta CS}$	Thermal Resistance, Case to Heat Sink (Typical)	0.5	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	62.5	

Package Marking and Ordering Information

Device Marking	Device	Package	Eco Status	Packaging Type	Quantity
FCPF260N60E	FCPF260N60E_F152	TO-220F	Green 	Tube	50

For Fairchild's definition of "green" Eco Status, please visit: http://www.fairchildsemi.com/company/green/rohs_green.html.

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$V_{GS} = 0V, I_D = 10mA, T_J = 25^\circ\text{C}$	600	-	-	V
		$V_{GS} = 0V, I_D = 10mA, T_J = 150^\circ\text{C}$	650	-	-	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 10mA$, Referenced to 25°C	-	0.67	-	$V/^\circ\text{C}$
BV_{DS}	Drain-Source Avalanche Breakdown Voltage	$V_{GS} = 0V, I_D = 15A$	-	700	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 480V, V_{GS} = 0V$	-	-	10	μA
		$V_{DS} = 480V, T_C = 125^\circ\text{C}$	-	-	10	
I_{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	± 100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$	2.5	-	3.5	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10V, I_D = 7.5A$	-	0.22	0.26	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 20V, I_D = 7.5A$	-	15.5	-	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V$ $f = 1\text{MHz}$	-	1880	2500	pF
C_{oss}	Output Capacitance		-	1330	1770	pF
C_{rss}	Reverse Transfer Capacitance		-	85	130	pF
C_{oss}	Output Capacitance	$V_{DS} = 380V, V_{GS} = 0V, f = 1\text{MHz}$	-	32	-	pF
$C_{oss \text{ eff.}}$	Effective Output Capacitance	$V_{DS} = 0V \text{ to } 480V, V_{GS} = 0V$	-	129	-	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	$V_{DS} = 380V, I_D = 7.5A$ $V_{GS} = 10V$ (Note 4)	-	48	62	nC
Q_{gs}	Gate to Source Gate Charge		-	7.4	-	nC
Q_{gd}	Gate to Drain "Miller" Charge		-	17	-	nC
ESR	Equivalent Series Resistance	$f = 1\text{MHz}$	-	5.8	-	Ω

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 380V, I_D = 7.5A$ $V_{GS} = 10V, R_G = 4.7\Omega$ (Note 4)	-	20	50	ns
t_r	Turn-On Rise Time		-	11	32	ns
$t_{d(off)}$	Turn-Off Delay Time		-	89	188	ns
t_f	Turn-Off Fall Time		-	13	36	ns

Drain-Source Diode Characteristics

I _S	Maximum Continuous Drain to Source Diode Forward Current	-	-	15	A	
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current	-	-	45	A	
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _{SD} = 7.5A	-	-	1.2	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0V, I _{SD} = 7.5A dI _F /dt = 100A/μs	-	270	-	ns
Q _{rr}	Reverse Recovery Charge		-	3.6	-	μC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $I_{AS} = 3A, V_{DD} = 50V, R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 7.5A, di/dt \leq 200A/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

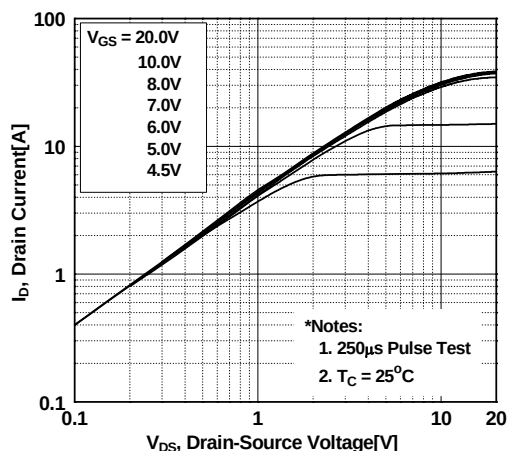


Figure 2. Transfer Characteristics

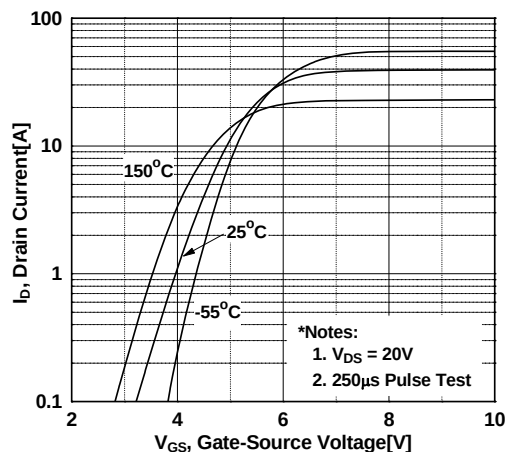


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

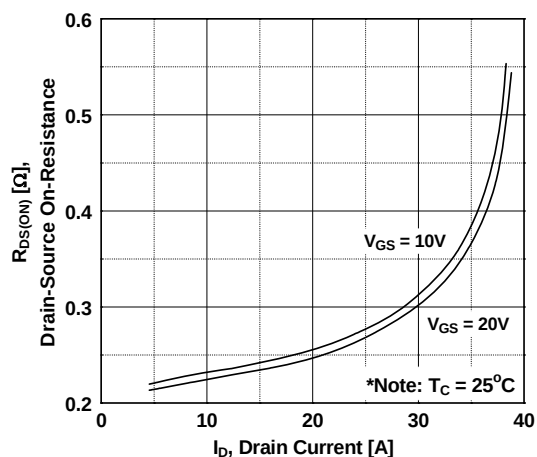


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

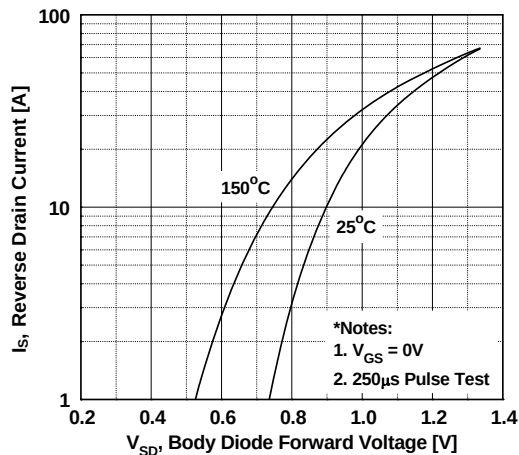


Figure 5. Capacitance Characteristics

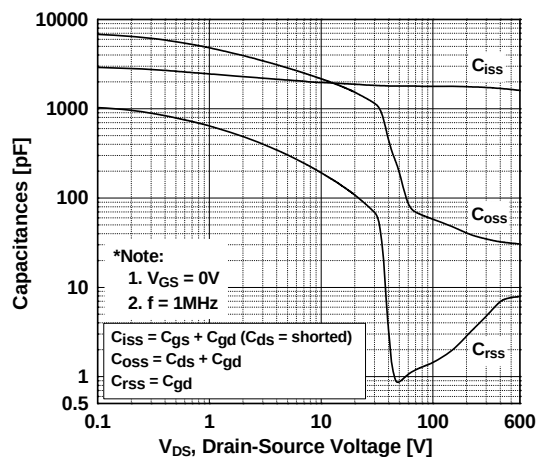
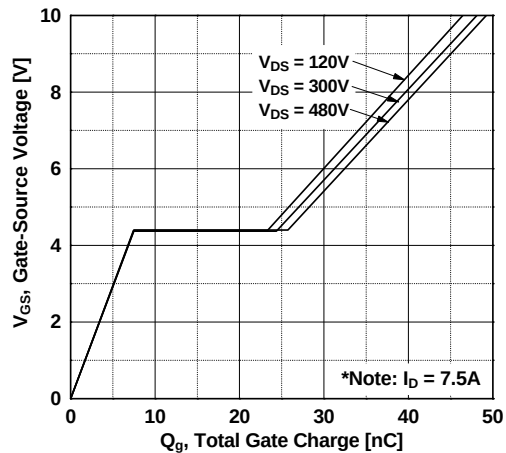


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

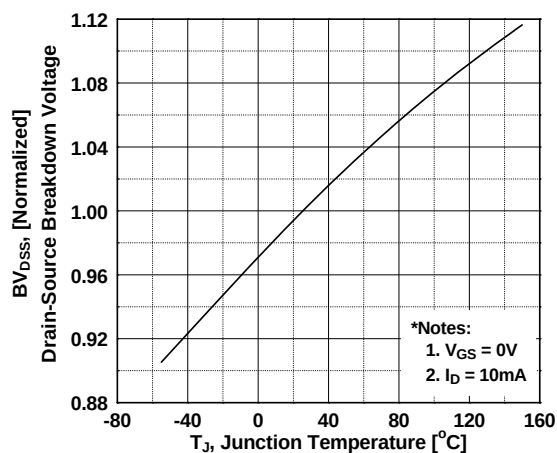


Figure 8. On-Resistance Variation vs. Temperature

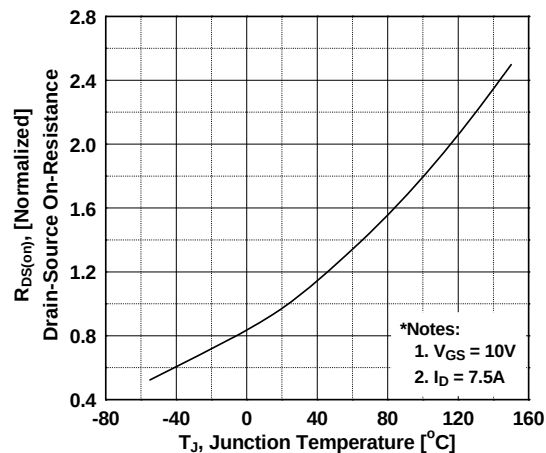


Figure 9. Maximum Safe Operating Area vs. Case Temperature

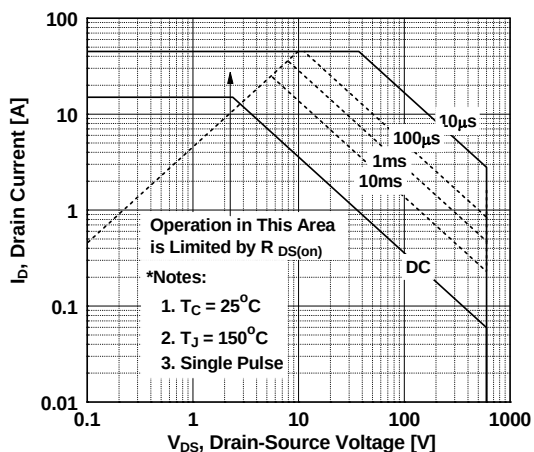


Figure 10. E_oss vs. Drain to Source Voltage Switching Capability

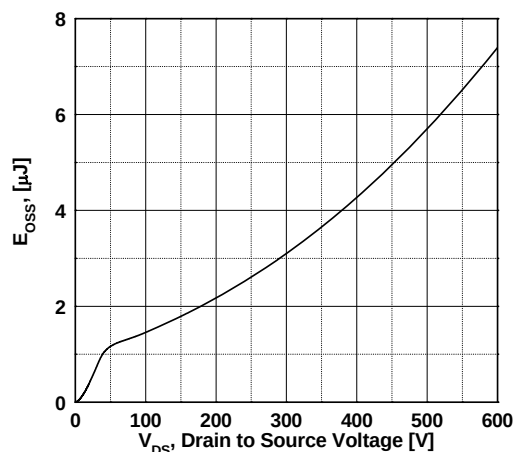
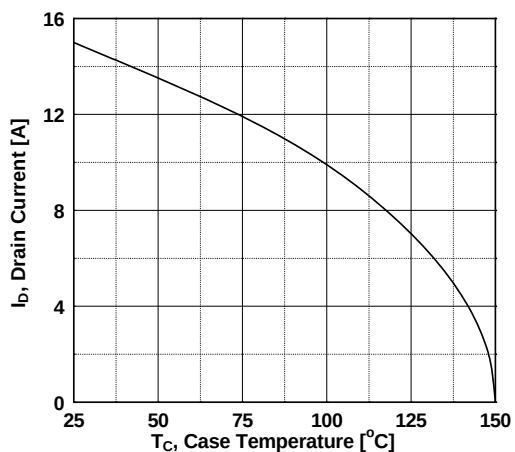
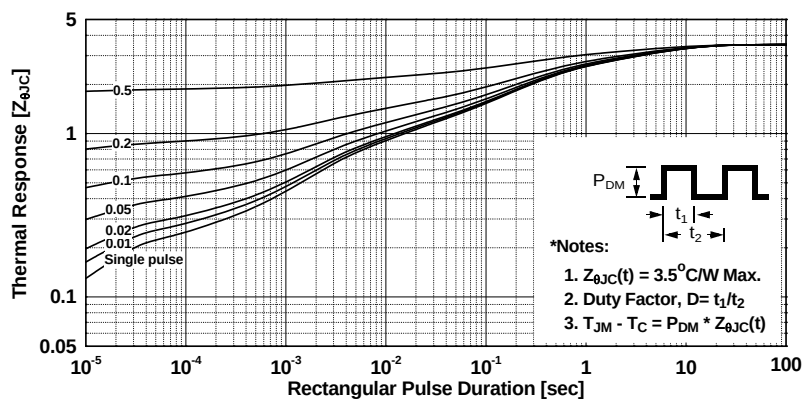


Figure 11. Maximum Drain Current

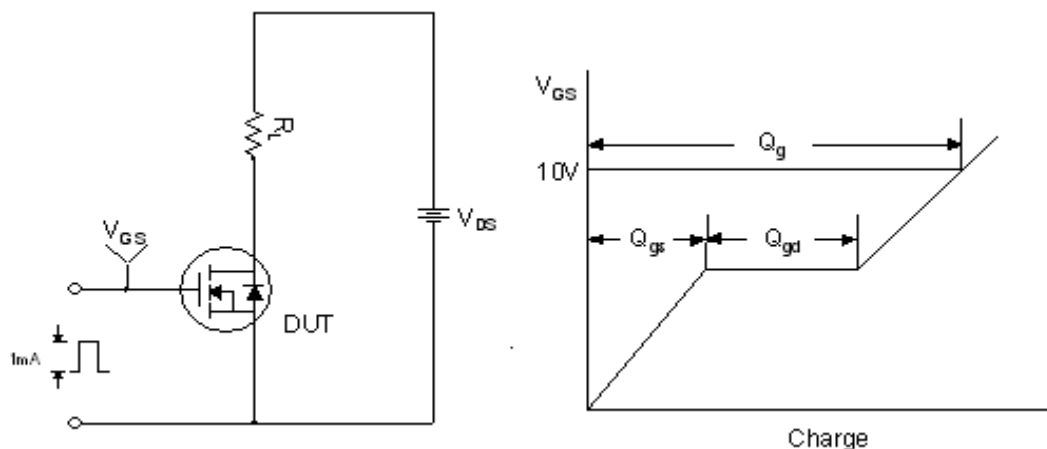


Typical Performance Characteristics (Continued)

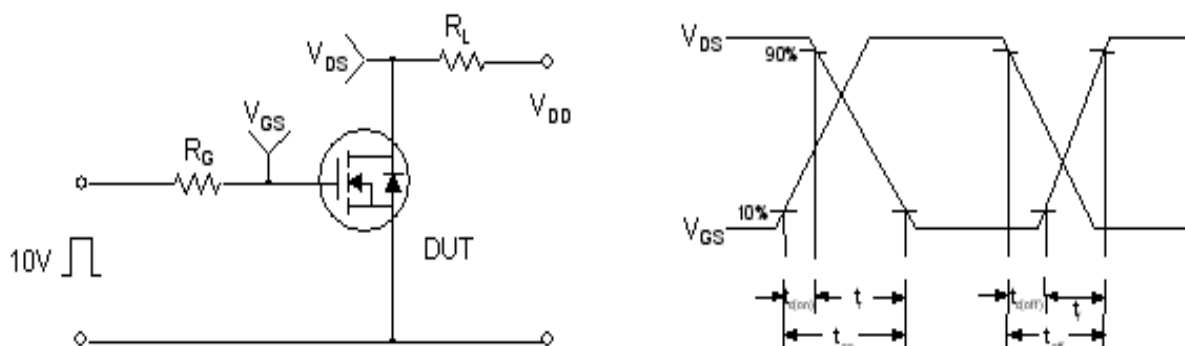
Figure 12. Transient Thermal Response Curve



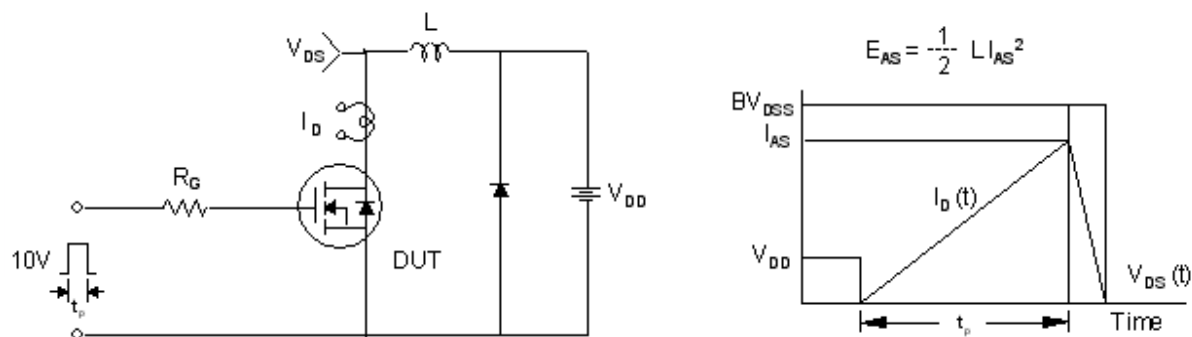
Gate Charge Test Circuit & Waveform

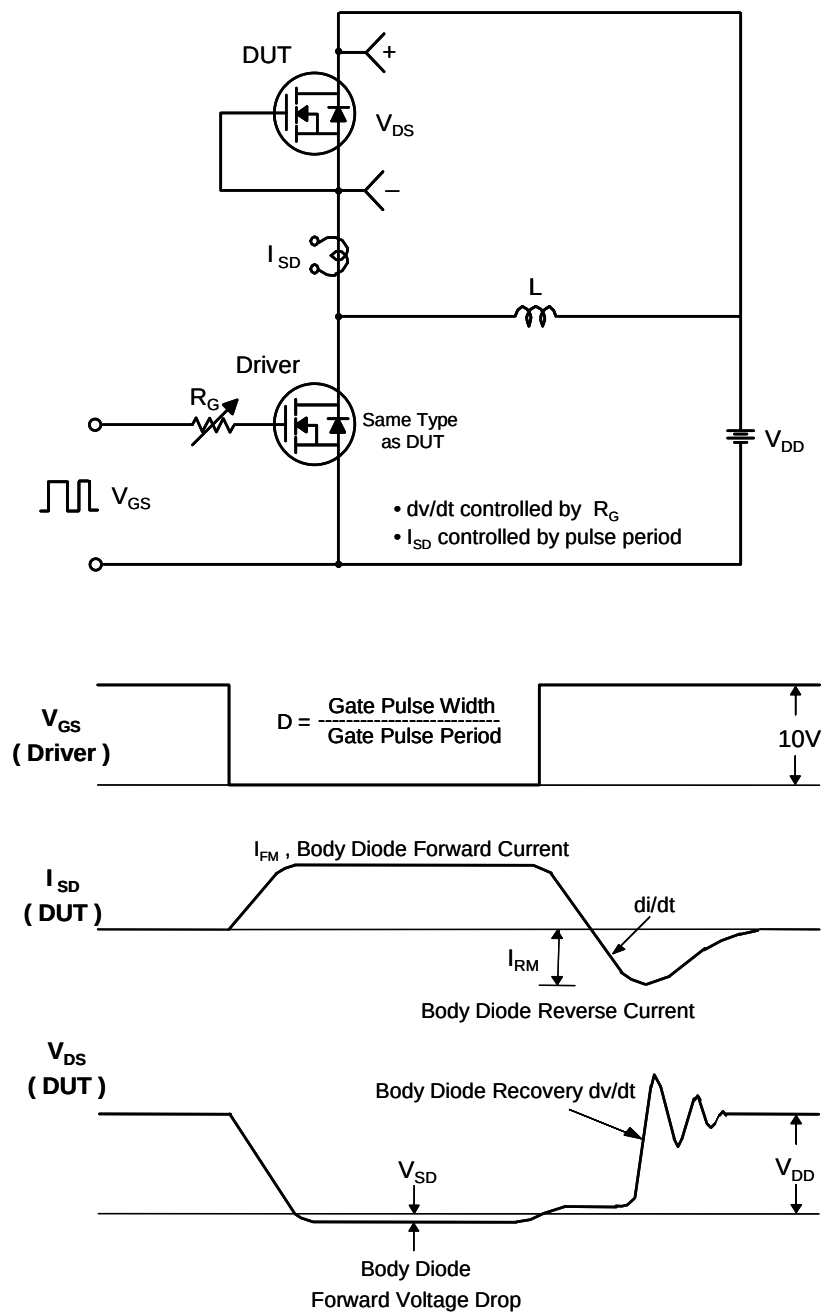


Resistive Switching Test Circuit & Waveforms



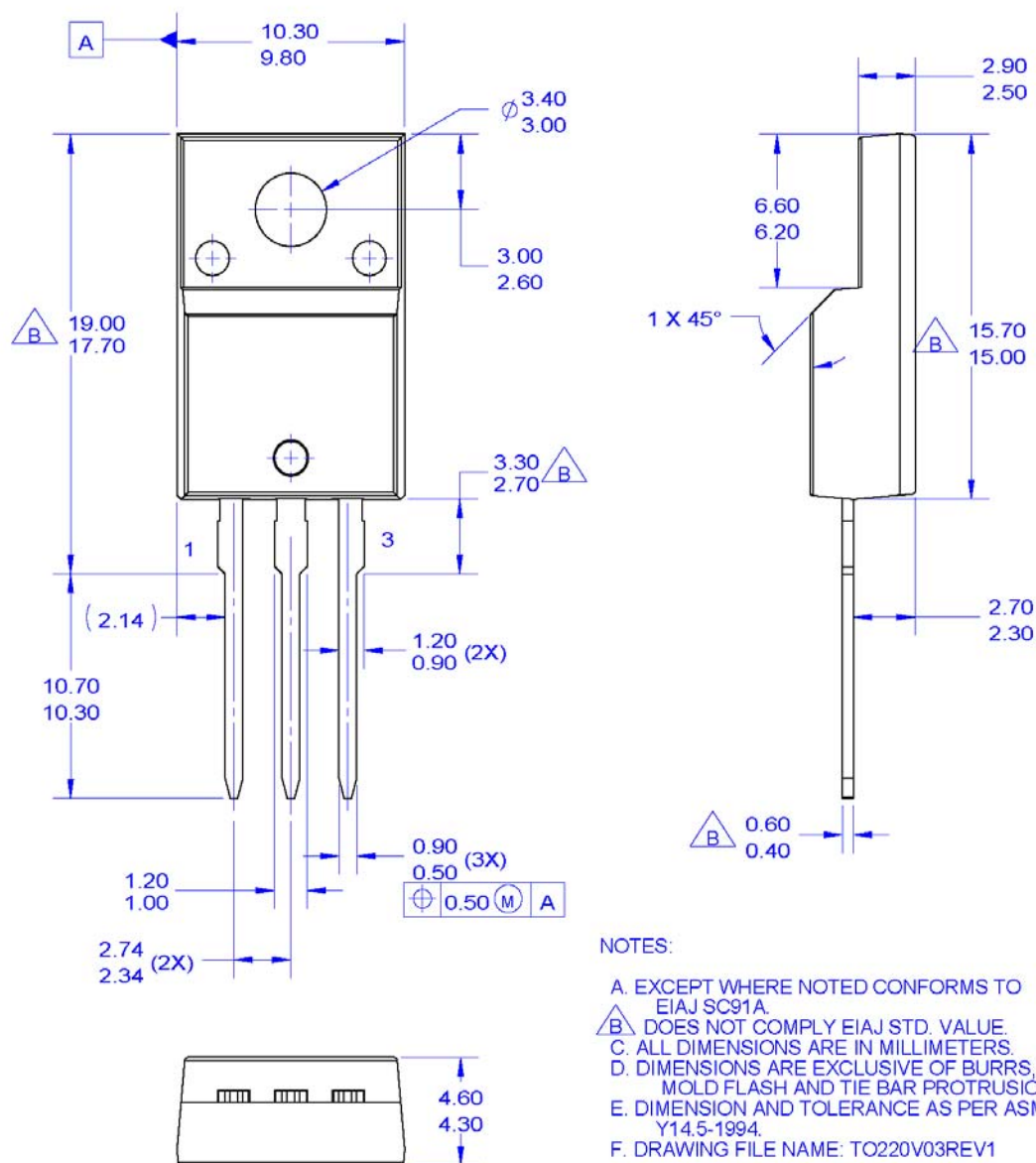
Unclamped Inductive Switching Test Circuit & Waveforms



Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

TO-220F



* Front/Back Side Isolation Voltage : AC 2500V

TO-220, MOLDED, 3LD, FULL PACK, EIAJ SC91

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